

PM75CSE120

FLAT-BASE TYPE
INSULATED PACKAGE

PM75CSE120



FEATURE

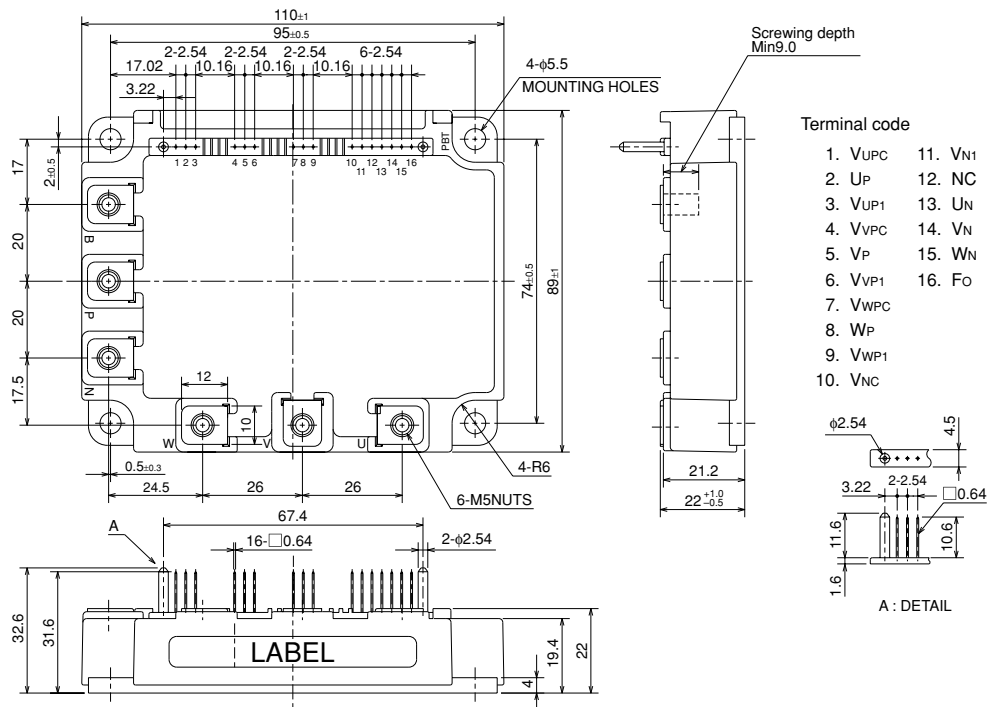
- a) Adopting new 4th generation planar IGBT chip, which performance is improved by 1 μ m fine rule process.
- b) Using new Diode which is designed to get soft reverse recovery characteristics.
- 3 ϕ 75A, 1200V Current-sense IGBT for 15kHz switching
- Monolithic gate drive & protection logic
- Detection, protection & status indication circuits for over-current, short-circuit, over-temperature & under-voltage
- Acoustic noise-less 11/15kW class inverter application
- UL Recognized Yellow Card No.E80276(N)
FileNo.E80271

APPLICATION

General purpose inverter, servo drives and other motor controls

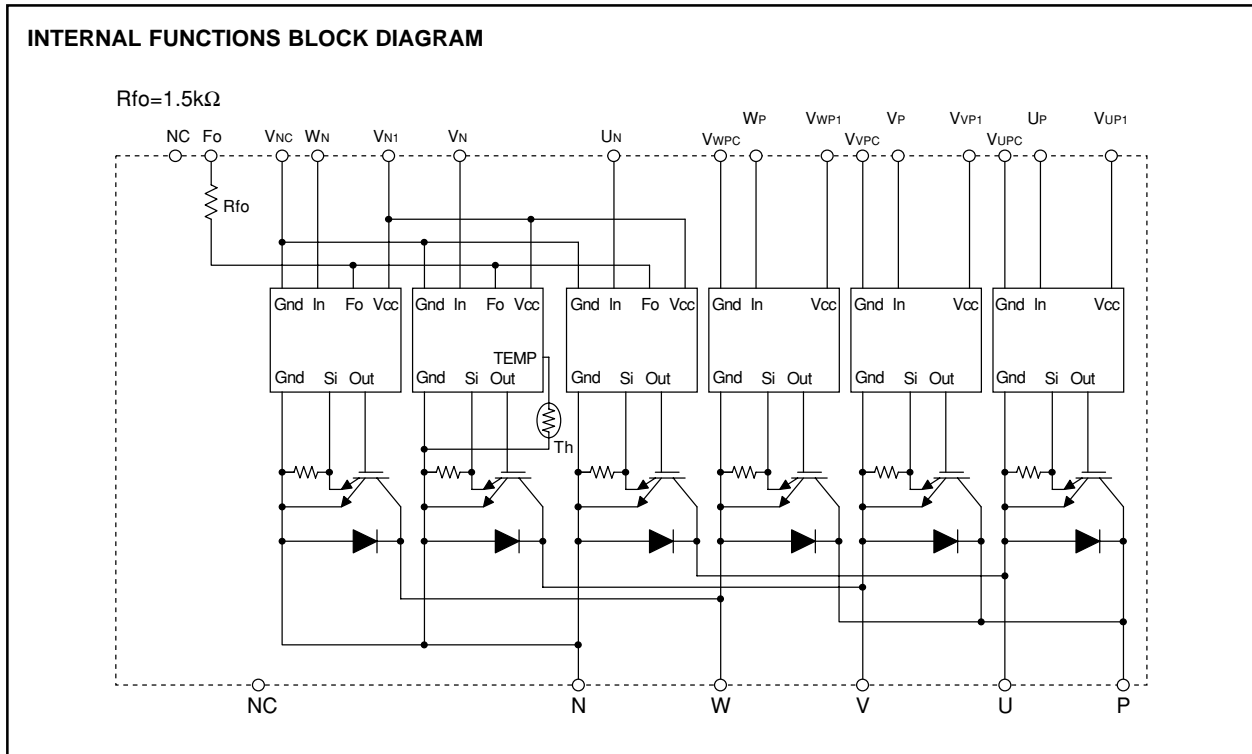
PACKAGE OUTLINES

Dimensions in mm



PM75CSE120

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INSULATED PACKAGE



MAXIMUM RATINGS (Tj = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
V _{CES}	Collector-Emitter Voltage	V _D = 15V, V _{CIN} = 15V	1200	V
±I _C	Collector Current	T _C = 25°C	75	A
±I _{CP}	Collector Current (Peak)	T _C = 25°C	150	A
P _C	Collector Dissipation	T _C = 25°C	416	W
T _j	Junction Temperature		-20 ~ +150	°C

CONTROL PART

Symbol	Parameter	Condition	Ratings	Unit
V _D	Supply Voltage	Applied between : V _{UP1} -V _{UPC} V _{Vp1} -V _{VPC} , V _{Wp1} -V _{WPC} , V _{N1} -V _{Nc}	20	V
V _{CIN}	Input Voltage	Applied between : U _P -V _{UPC} , V _P -V _{VPC} W _P -V _{WPC} , U _N • V _N • W _N -V _{Nc}	20	V
V _{FO}	Fault Output Supply Voltage	Applied between : F _O -V _{Nc}	20	V
I _{FO}	Fault Output Current	Sink current at F _O terminal	20	mA

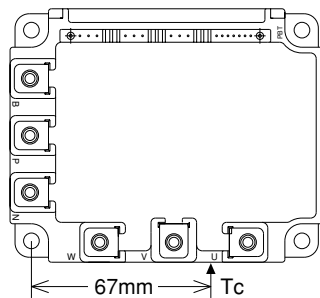
PM75CSE120

FLAT-BASE TYPE
INSULATED PACKAGE

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
V _{CC(prot)}	Supply Voltage Protected by OC & SC	V _D = 13.5 ~ 16.5V, Inverter Part, T _j = 125°C Start	800	V
V _{CC(surge)}	Supply Voltage (Surge)	Applied between : P-N, Surge value or without switching	1000	V
T _c	Module Case Operating Temperature	(Note-1)	-20 ~ +100	°C
T _{stg}	Storage Temperature		-40 ~ +125	°C
V _{iso}	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base, AC 1 min.	2500	V _{rms}

(Note-1) T_c measurement point is as shown below. (Base plate depth 3mm)



THERMAL RESISTANCES

Symbol	Parameter	Test Condition	Limits			Unit
			Min.	Typ.	Max.	
R _{th(j-c)Q}	Junction to case Thermal Resistances	Inverter IGBT part (per 1 element), (Note-1)	—	—	0.30	°C/W
R _{th(j-c)F}		Inverter FWDi part (per 1 element), (Note-1)	—	—	0.47	
R _{th(j-c)Q}		Inverter IGBT part (per 1 element), (Note-2)	—	—	0.17	
R _{th(j-c)F}		Inverter FWDi part (per 1 element), (Note-2)	—	—	0.27	
R _{th(c-f)}	Contact Thermal Resistance	Case to fin, Thermal grease applied (per 1 module)	—	—	0.027	

(Note-2) T_c measurement point is just under the chips.
If you use this value, R_{th(f-a)} should be measured just under the chips.

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Test Condition	Limits			Unit	
			Min.	Typ.	Max.		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _D = 15V, I _C = 75A V _{CIN} = 0V, Pulsed (Fig. 1)	T _j = 25°C	—	2.4	3.2	V
			T _j = 125°C	—	2.1	2.8	
V _{EC}	FWDi Forward Voltage	-I _C = 75A, V _D = 15V, V _{CIN} = 15V (Fig. 2)	—	2.5	3.5	V	
t _{on}	Switching Time	V _D = 15V, V _{CIN} = 15V↔0V V _{CC} = 600V, I _C = 75A T _j = 125°C Inductive Load (upper and lower arm) (Fig. 3)	0.5	1.0	2.5	μs	
t _{tr}			—	0.15	0.3		
t _{c(on)}			—	0.4	1.0		
t _{off}			—	2.5	3.5		
t _{c(off)}			—	0.7	1.2		
I _{CES}	Collector-Emitter Cutoff Current	V _{CE} = V _{CE(s)} , V _{CIN} = 15V (Fig. 4)	T _j = 25°C	—	—	1	mA
			T _j = 125°C	—	—	10	

PM75CSE120

FLAT-BASE TYPE
INSULATED PACKAGE

CONTROL PART

Symbol	Parameter	Test Condition	Limits			Unit	
			Min.	Typ.	Max.		
Id	Circuit Current	VD = 15V, VCIN = 15V	VN1-VNC	—	45	62	mA
			VXP1-VXPC	—	15	20	
Vth(on)	Input ON Threshold Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC	1.2	1.5	1.8	V	
Vth(off)	Input OFF Threshold Voltage	UN • VN • WN-VNC	1.7	2.0	2.3		
OC	Over Current Trip Level	VD = 15V (Fig. 5.6)	Tj = 25°C	156	238	—	A
			Tj = 125°C	105	—	—	
SC	Short Circuit Trip Level	-20 ≤ Tj ≤ 125°C, VD = 15V (Fig. 5.6)	—	250	—	A	
toff(OC)	Over Current Delay Time	VD = 15V (Fig. 5.6)	—	10	—	μs	
OT	Over Temperature Protection	Base-plate Temperature detection, VD = 15V	Trip level	111	118	125	°C
			Reset level	—	100	—	
UV	Supply Circuit Under-Voltage Protection	-20 ≤ Tj ≤ 125°C	Trip level	11.5	12.0	12.5	V
			Reset level	—	12.5	—	
Ifo(H)	Fault Output Current	VD = 15V, VFO = 15V (Note-3)	—	—	0.01	mA	
Ifo(L)			—	10	15		
tFO	Minimum Fault Output Pulse Width	VD = 15V (Note-3)	1.0	1.8	—	ms	

(Note-3) Fault output is given only when the internal OC, SC, OT & UV protection.
 Fault output of OT protection operate by lower arm.
 Fault output of OC, SC protection given pulse.
 Fault output of OT, UV protection given pulse while over level.

MECHANICAL RATINGS AND CHARACTERISTICS

Symbol	Parameter	Test Condition	Limits			Unit
			Min.	Typ.	Max.	
—	Mounting torque	Main terminal screw : M5	2.5	3.0	3.5	N • m
—	Mounting torque	Mounting part screw : M5	2.5	3.0	3.5	N • m
—	Weight	—	—	560	—	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Test Condition	Recommended value	Unit
Vcc	Supply Voltage	Applied across P-N terminals	≤ 800	V
VD	Control Supply Voltage	Applied between : VUP1-VUPC, VVP1-VVPC VWP1-VWPC, VN1-VNC (Note-4)	15 ± 1.5	V
VCIN(on)	Input ON Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC UN • VN • WN-VNC	≤ 0.8	V
VCIN(off)	Input OFF Voltage		≥ 4.0	
fPWM	PWM Input Frequency	Using Application Circuit input signal of IPM, 3φ sinusoidal PWM VVVF inverter (Fig. 8)	≤ 20	kHz
tdead	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 3.0	μs

(Note-4) Allowable Ripple rating of Control Voltage : dv/dt ≤ ±5V/μs, 2Vp-p

PM75CSE120

FLAT-BASE TYPE
INSULATED PACKAGE

PRECAUTIONS FOR TESTING

1. Before applying any control supply voltage (V_D), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state.
After this, the specified ON and OFF level setting for each input signal should be done.
2. When performing "OC" and "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above V_{CES} rating of the device.
(These test should not be done by using a curve tracer or its equivalent.)

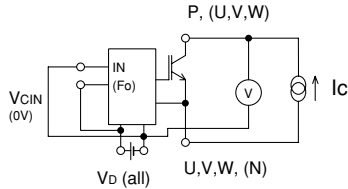


Fig. 1 $V_{CE(sat)}$ Test

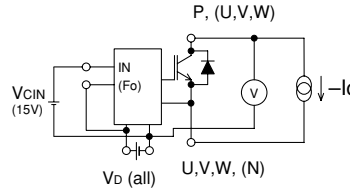
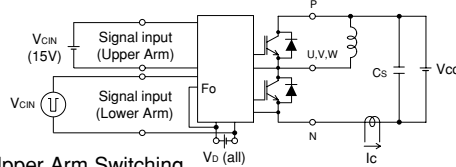


Fig. 2 V_{EC} Test

a) Lower Arm Switching



b) Upper Arm Switching

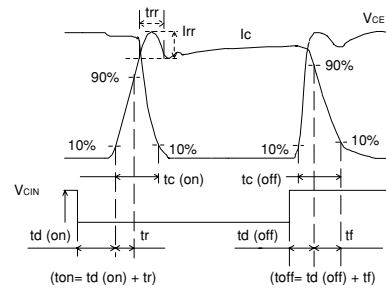
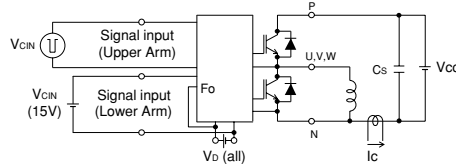


Fig. 3 Switching time Test circuit and waveform

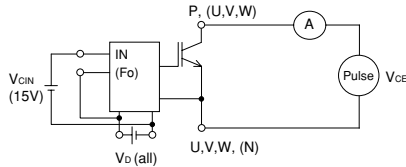


Fig. 4 I_{CES} Test

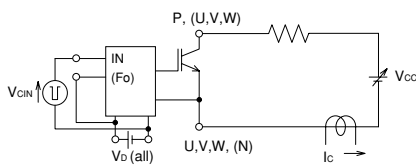


Fig. 5 OC and SC Test

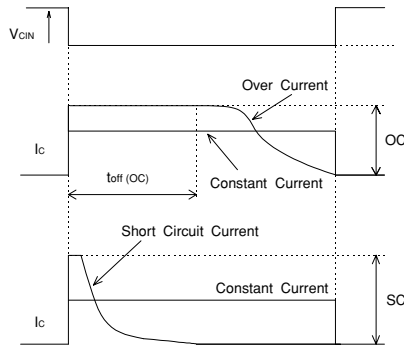


Fig. 6 OC and SC Test waveform

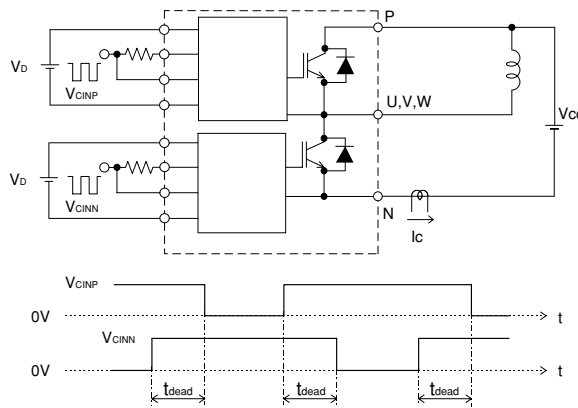


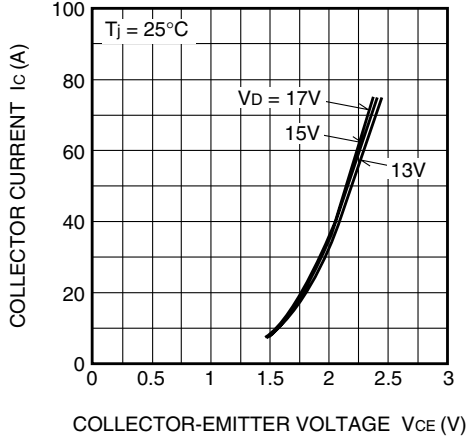
Fig. 7 Dead time measurement point example

PM75CSE120

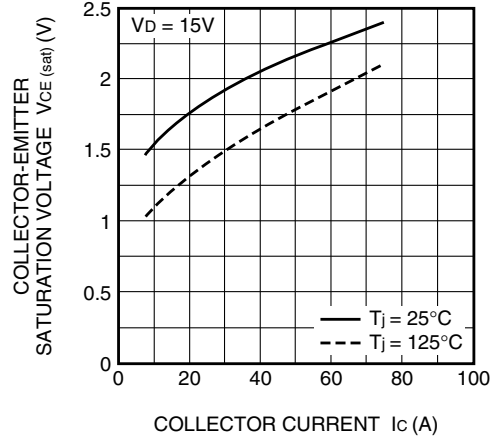
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PERFORMANCE CURVES

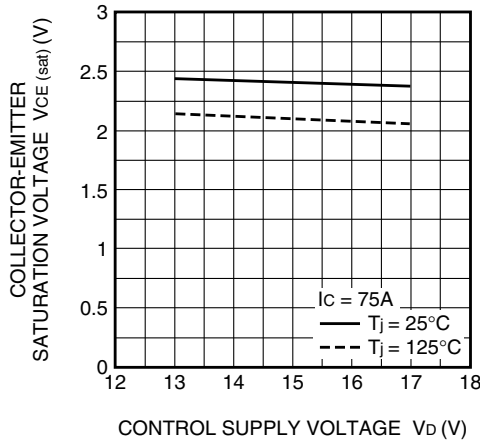
OUTPUT CHARACTERISTICS
(TYPICAL)



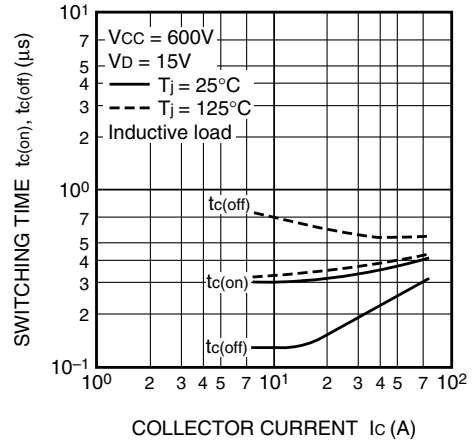
COLLECTOR-EMITTER SATURATION
VOLTAGE (VS. I_c) CHARACTERISTICS
(TYPICAL)



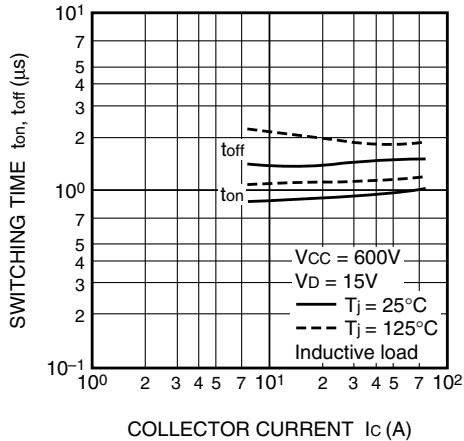
COLLECTOR-EMITTER SATURATION
VOLTAGE (VS. V_b) CHARACTERISTICS
(TYPICAL)



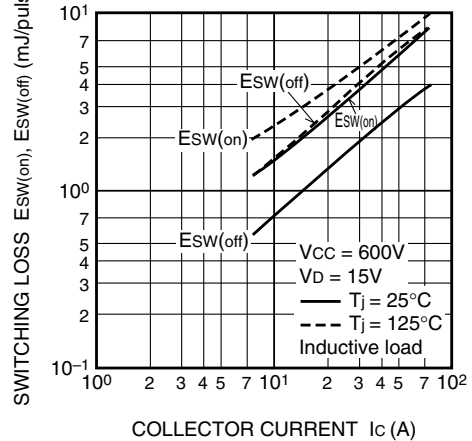
SWITCHING TIME CHARACTERISTICS
(TYPICAL)



SWITCHING TIME CHARACTERISTICS
(TYPICAL)



SWITCHING LOSS CHARACTERISTICS
(TYPICAL)



PM75CSE120

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